

THE SPECIFICATION OF AlGaAs IR LED CHIP "I56J"

1. DESCRIPTION

This is a AlGaAs infrared LED chip. It is N-side up. The peak wavelength is 850 nm (Typ.).

2. ELECTRO - OPTICAL CHARACTERISTICS (Ta=25deg. C)

CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage (Vf) IF=20mA		1.45		V
Reverse Voltage (Vr) IR=10μA	5			V
Radiated Power ¹⁾ (Po) IF=20mA	4.5			mW
Peak Wavelength (λp) IF=20mA		850		nm
Spectral Radiation Bandwidth (Δλ) IF=20mA		40		nm

1) LED chip is mounted on TO-18 gold header without resin coated.

3. ABSOLUTE MAXIMUM RATINGS

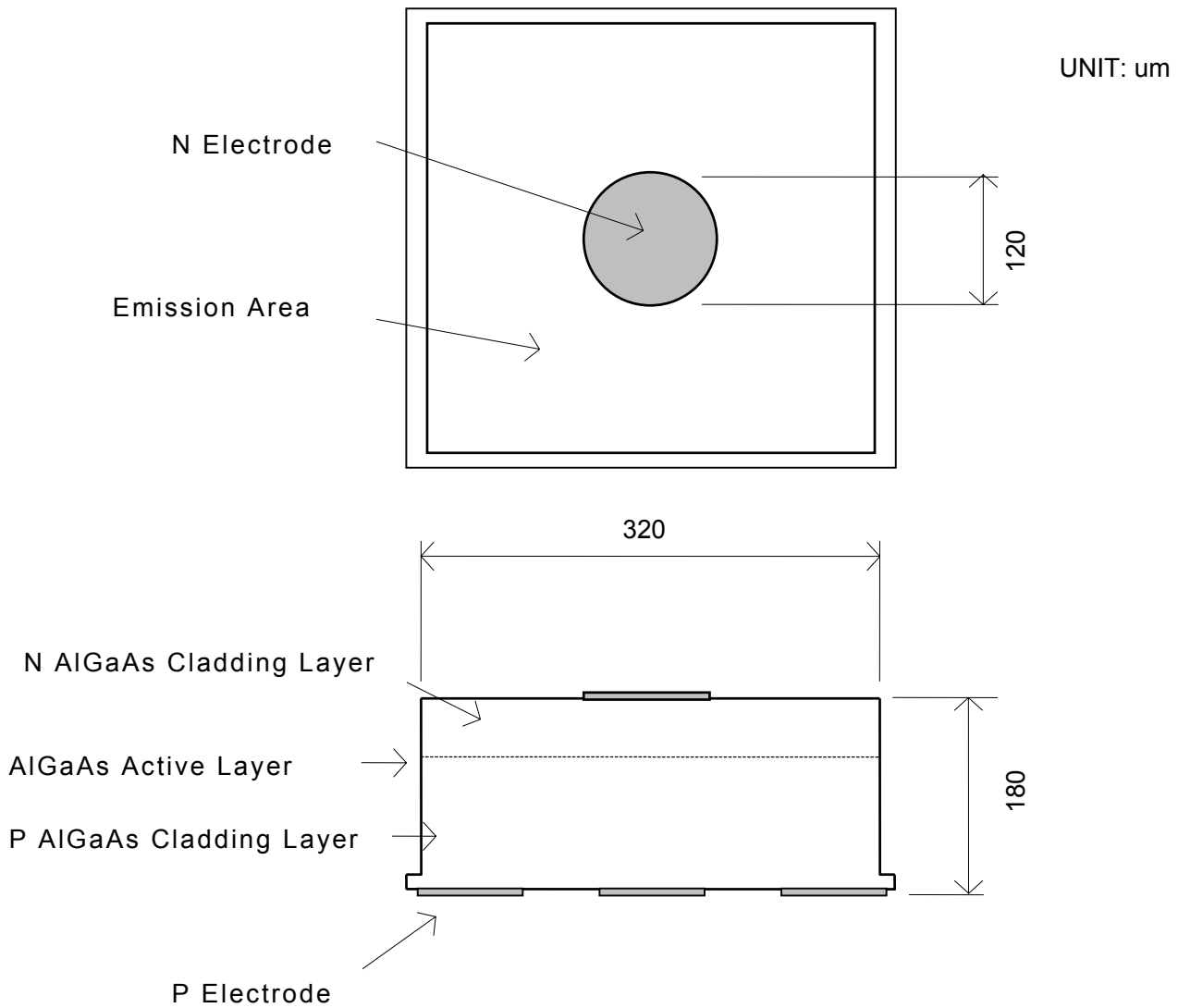
Continuous Maximum Forward Current	: 100 mA(DC)
Reverse Voltage	: 5 V(IR=10μA)
Storage Temperature	
while on mylar membrane	: 0 to 40 deg. C
after removal from mylar membrane	: -40 to 100 deg. C

4. PHYSICAL CHARACTERISTICS AND STRUCTURE

1)Material	: AlGaAs
2)Structure	: Double Hetero Structure
3)Junction Size	: 0.320mmX0.320mm
4)Thickness	: 0.180mm
5)Bond Pad Size	: 0.120mm diameter
6)Anode Metallization	: Gold Alloy
7)Cathode Metallization	: Gold Alloy

Physical Dimensions

Model I56J



Remark: This specification is for reference purpose only, and subject to change without prior notice.
Approved specification shall be obtained for the regular purchase.